

John M Dell

List of Publications by Year in descending order

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papers

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201674

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271
times ranked

2489
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#	ARTICLE	IF	CITATIONS
1	Effect of deposition conditions on mechanical properties of low-temperature PECVD silicon nitride films. <i>Materials Science & Engineering A: Structural Materials: Properties, Microstructure and Processing</i> , 2006, 435-436, 453-459.	5.6	161
2	Scattering mechanisms limiting two-dimensional electron gas mobility in Al _{0.25} Ga _{0.75} N/GaN modulation-doped field-effect transistors. <i>Journal of Applied Physics</i> , 2000, 87, 3900-3904.	2.5	126
3	Widely Tunable MEMS-Based Fabry-Pérot Filter. <i>Journal of Microelectromechanical Systems</i> , 2009, 18, 905-913.	2.5	106
4	⁶⁰ Co gamma irradiation effects on n-GaN Schottky diodes. <i>IEEE Transactions on Electron Devices</i> , 2003, 50, 2326-2334.	3.0	96
5	Nanoscratch-induced phase transformation of monocrystalline Si. <i>Scripta Materialia</i> , 2010, 63, 847-850.	5.2	86
6	MEMS-based microspectrometer technologies for NIR and MIR wavelengths. <i>Journal Physics D: Applied Physics</i> , 2009, 42, 133001.	2.8	80
7	Determination of mechanical properties of PECVD silicon nitride thin films for tunable MEMS Fabry-Pérot optical filters. <i>Journal of Micromechanics and Microengineering</i> , 2005, 15, 608-614.	2.6	71
8	⁶⁰ Co gamma-irradiation-induced defects in n-GaN. <i>Applied Physics Letters</i> , 2002, 80, 4354-4356.	3.3	66
9	Quantifying the Effects of 16p11.2 Copy Number Variants on Brain Structure: A Multisite Genetic-First Study. <i>Biological Psychiatry</i> , 2018, 84, 253-264.	1.3	56
10	Monolithic integration of an infrared photon detector with a MEMS-based tunable filter. <i>IEEE Electron Device Letters</i> , 2005, 26, 888-890.	3.9	54
11	HgCdTe mid-wavelength IR photovoltaic detectors fabricated using plasma induced junction technology. <i>Journal of Electronic Materials</i> , 2000, 29, 841-848.	2.2	53
12	Nanoscratch-induced deformation of single crystal silicon. <i>Journal of Vacuum Science & Technology B</i> , 2009, 27, 1374-1377.	1.3	48
13	Magnetic field dependent Hall data analysis of electron transport in modulation-doped AlGaIn/GaN heterostructures. <i>Journal of Applied Physics</i> , 1997, 82, 2996-3002.	2.5	47
14	Tunable Fabry-Pérot cavities fabricated from PECVD silicon nitride employing zinc sulphide as the sacrificial layer. <i>Journal of Micromechanics and Microengineering</i> , 2001, 11, 589-594.	2.6	46
15	GaSb: A New Alternative Substrate for Epitaxial Growth of HgCdTe. <i>Journal of Electronic Materials</i> , 2014, 43, 2788-2794.	2.2	43
16	Mechanisms of infrared photoluminescence in HgTe/HgCdTe superlattice. <i>Journal of Applied Physics</i> , 2012, 112, 063512.	2.5	37
17	MBE Growth of Mid-wave Infrared HgCdTe Layers on GaSb Alternative Substrates. <i>Journal of Electronic Materials</i> , 2015, 44, 3180-3187.	2.2	37
18	Characterization of Hg _{0.7} Cd _{0.3} Te n- on p-type structures obtained by reactive ion etching induced p- to n conversion. <i>Journal of Electronic Materials</i> , 2000, 29, 837-840.	2.2	36

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19	Generation-recombination effects on dark currents in CdTe-passivated midwave infrared HgCdTe photodiodes. <i>Journal of Applied Physics</i> , 2005, 98, 014504.	2.5	36
20	Stress in low-temperature plasma enhanced chemical vapour deposited silicon nitride thin films. <i>Smart Materials and Structures</i> , 2006, 15, S29-S38.	3.5	36
21	Interpretation of current flow in photodiode structures using laser beam-induced current for characterization and diagnostics. <i>IEEE Transactions on Electron Devices</i> , 2006, 53, 23-31.	3.0	33
22	Development of an Alkaline-Compatible Porous-Silicon Photolithographic Process. <i>Journal of Microelectromechanical Systems</i> , 2011, 20, 418-423.	2.5	32
23	Junction depth measurement in HgCdTe using laser beam induced current (LBIC). <i>Journal of Electronic Materials</i> , 1999, 28, 603-610.	2.2	29
24	Effect of oxidation on the chemical bonding structure of PECVD SiNx thin films. <i>Journal of Applied Physics</i> , 2006, 100, 123516.	2.5	29
25	Nanoindentation of HgCdTe prepared by molecular beam epitaxy. <i>Applied Physics Letters</i> , 2005, 87, 251905.	3.3	28
26	Effects of deposition temperature on the mechanical and physical properties of silicon nitride thin films. <i>Journal of Applied Physics</i> , 2005, 98, 044904.	2.5	28
27	p-to-n type-conversion mechanisms for HgCdTe exposed to H ₂ /CH ₄ plasmas. <i>Journal of Electronic Materials</i> , 2001, 30, 762-767.	2.2	27
28	Design and Characterization of Fabry-Pérot MEMS-Based Short-Wave Infrared Microspectrometers. <i>Journal of Electronic Materials</i> , 2008, 37, 1811-1820.	2.2	27
29	Uniform Dispersion of Lanthanum Hexaboride Nanoparticles in a Silica Thin Film: Synthesis and Optical Properties. <i>ACS Applied Materials & Interfaces</i> , 2012, 4, 5833-5838.	8.0	27
30	Large-Area MEMS Tunable Fabry-Pérot Filters for Multi/Hyperspectral Infrared Imaging. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2017, 23, 45-52.	2.9	27
31	Multi-heterojunction large area HgCdTe long wavelength infrared photovoltaic detector for operation at near room temperatures. <i>Journal of Electronic Materials</i> , 1998, 27, 740-746.	2.2	26
32	Diffusion length measurements in p-HgCdTe using laser beam induced current. <i>Journal of Electronic Materials</i> , 2001, 30, 696-703.	2.2	26
33	Mercury cadmium telluride resonant-cavity-enhanced photoconductive infrared detectors. <i>Applied Physics Letters</i> , 2005, 87, 211104.	3.3	26
34	Optical characterization of Fabry-Pérot MEMS filters integrated on tunable short-wave IR detectors. <i>IEEE Photonics Technology Letters</i> , 2006, 18, 1079-1081.	2.5	26
35	Poisson's Ratio of Low-Temperature PECVD Silicon Nitride Thin Films. <i>Journal of Microelectromechanical Systems</i> , 2007, 16, 622-627.	2.5	26
36	Characterization of Electrically Active Defects in Photovoltaic Detector Arrays Using Laser Beam-Induced Current. <i>IEEE Transactions on Electron Devices</i> , 2005, 52, 2163-2174.	3.0	25

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37	Depth Profiling of Electronic Transport Parameters in n-on-p Boron-Ion-Implanted Vacancy-Doped HgCdTe. <i>Journal of Electronic Materials</i> , 2013, 42, 3108-3113.	2.2	25
38	Analysis of crosstalk in HgCdTe p-on-n heterojunction photovoltaic infrared sensing arrays. <i>Journal of Electronic Materials</i> , 1999, 28, 617-623.	2.2	24
39	Dark currents in long wavelength infrared HgCdTe gated photodiodes. <i>Journal of Electronic Materials</i> , 2004, 33, 621-629.	2.2	23
40	Transport properties of reactive-ion-etching-induced p-to-n type converted layers in HgCdTe. <i>Journal of Electronic Materials</i> , 2002, 31, 652-659.	2.2	22
41	Abnormal auditory mismatch fields in adults with autism spectrum disorder. <i>Neuroscience Letters</i> , 2019, 698, 140-145.	2.1	22
42	A novel multi-heterojunction HgCdTe long-wavelength infrared photovoltaic detector for operation under reduced cooling conditions. <i>Semiconductor Science and Technology</i> , 1998, 13, 1209-1214.	2.0	21
43	Low temperature saturation of p-n junction laser beam induced current signals. <i>Solid-State Electronics</i> , 2004, 48, 409-414.	1.4	21
44	Laser beam induced current as a tool for HgCdTe photodiode characterisation. <i>Microelectronics Journal</i> , 2000, 31, 537-544.	2.0	20
45	Scanning laser microscopy of reactive ion etching induced n-type conversion in vacancy-doped p-type HgCdTe. <i>Applied Physics Letters</i> , 1997, 70, 3443-3445.	3.3	19
46	Estimation of doping density in HgCdTe p-n junctions using scanning laser microscopy. <i>Applied Physics Letters</i> , 1998, 72, 52-54.	3.3	19
47	Delayed Auditory Evoked Responses in Autism Spectrum Disorder across the Life Span. <i>Developmental Neuroscience</i> , 2019, 41, 223-233.	2.0	19
48	Mercury annealing of reactive ion etching induced p- to n-type conversion in extrinsically doped p-type HgCdTe. <i>Journal of Applied Physics</i> , 1998, 83, 5555-5557.	2.5	18
49	Contribution of hole trap to persistent photoconductivity in n-type GaN. <i>Journal of Applied Physics</i> , 2004, 96, 1019-1023.	2.5	18
50	Environmental stability and cryogenic thermal cycling of low-temperature plasma-deposited silicon nitride thin films. <i>Journal of Applied Physics</i> , 2006, 99, 053519.	2.5	18
51	Small two-dimensional arrays of mid-wavelength infrared HgCdTe diodes fabricated by reactive ion etching-induced p-to-n-type conversion. <i>Journal of Electronic Materials</i> , 2003, 32, 627-632.	2.2	17
52	Annealing of C60o gamma radiation-induced damage in n-GaN Schottky barrier diodes. <i>Journal of Applied Physics</i> , 2007, 101, 054511.	2.5	17
53	Investigation of 1/f Noise Mechanisms in Midwave Infrared HgCdTe Gated Photodiodes. <i>Journal of Electronic Materials</i> , 2007, 36, 884-889.	2.2	17
54	Model and Analysis of a High Sensitivity Resonant Optical Read-Out Approach Suitable for Cantilever Sensor Arrays. <i>Journal of Lightwave Technology</i> , 2012, 30, 1863-1868.	4.6	17

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55	MEMS-Based Tunable Fabry-Perot Filters for Adaptive Multispectral Thermal Imaging. <i>Journal of Microelectromechanical Systems</i> , 2016, 25, 227-235.	2.5	17
56	Evaluation of III-V multilayer transport parameters using quantitative mobility spectrum analysis. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 1997, 44, 65-69.	3.5	16
57	HgCdTe long-wavelength infrared photovoltaic detectors fabricated using plasma-induced junction formation technology. <i>Journal of Electronic Materials</i> , 2003, 32, 615-621.	2.2	15
58	Passivation effects on reactive-ion-etch-formed n-on-p junctions in HgCdTe. <i>Journal of Electronic Materials</i> , 2002, 31, 743-748.	2.2	14
59	Mercury cadmium telluride/cadmium telluride distributed bragg reflectors for use with resonant cavity-enhanced detectors. <i>Journal of Electronic Materials</i> , 2005, 34, 710-715.	2.2	14
60	Dielectric thin films for MEMS-based optical sensors. <i>Microelectronics Reliability</i> , 2007, 47, 733-738.	1.7	14
61	On-chip read-out of picomechanical motion under ambient conditions. <i>Nanoscale</i> , 2015, 7, 1927-1933.	5.6	14
62	Planar p-on-n HgCdTe heterojunction mid-wavelength infrared photodiodes formed using plasma-induced junction isolation. <i>Journal of Electronic Materials</i> , 2003, 32, 622-626.	2.2	13
63	Crystallization of silicon nitride thin films synthesized by plasma-enhanced chemical vapour deposition. <i>Scripta Materialia</i> , 2007, 57, 739-742.	5.2	13
64	Process Control of Cantilever Deflection for Sensor Application Based on Optical Waveguides. <i>Journal of Microelectromechanical Systems</i> , 2013, 22, 569-579.	2.5	13
65	Investigation of Cerium-Substituted Europium Iron Garnets Deposited by Biased Target Ion Beam Deposition. <i>IEEE Transactions on Magnetics</i> , 2014, 50, 1-7.	2.1	13
66	Ge/ZnS-Based Micromachined Fabry-Perot Filters for Optical MEMS in the Longwave Infrared. <i>Journal of Microelectromechanical Systems</i> , 2015, 24, 2109-2116.	2.5	13
67	Investigation of ICPECVD Silicon Nitride Films for HgCdTe Surface Passivation. <i>Journal of Electronic Materials</i> , 2015, 44, 2990-3001.	2.2	13
68	<title>Erasure of poling-induced second-order optical nonlinearities in silica by UV exposure</title>. , 1994, 2289, 185.		12
69	Correlation of laser-beam-induced current with current-voltage measurements in HgCdTe photodiodes. <i>Journal of Electronic Materials</i> , 2004, 33, 560-571.	2.2	12
70	Determination of mechanical properties of silicon nitride thin films using nanoindentation. , 2005, 5798, 216.		12
71	A monolithically integrated HgCdTe short-wavelength infrared photodetector and micro-electro-mechanical systems-based optical filter. <i>Journal of Electronic Materials</i> , 2005, 34, 716-721.	2.2	12
72	Oxidation of PECVD SiNx thin films. <i>Journal of Alloys and Compounds</i> , 2007, 437, 332-338.	5.5	12

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73	Effect of High-Density Plasma Process Parameters on Carrier Transport Properties in p-to-n Type Converted Hg _{0.7} Cd _{0.3} Te Layer. Journal of Electronic Materials, 2007, 36, 913-918.	2.2	12
74	Chemical resistance of porous silicon: photolithographic applications. Physica Status Solidi C: Current Topics in Solid State Physics, 2011, 8, 1847-1850.	0.8	12
75	<title>Isothermal vapor phase epitaxy as a versatile technology for infrared photodetectors</title> . , 1997, 2999, 34.		11
76	Simulation of mid-infrared HgTe/CdTe quantum-well vertical-cavity surface-emitting lasers. Journal of Applied Physics, 1998, 83, 4286-4291.	2.5	11
77	HgCdTe photovoltaic detectors fabricated using a new junction formation technology. Microelectronics Journal, 2000, 31, 545-551.	2.0	11
78	Towards MEMS-based infrared tunable microspectrometers. , 2002, 4935, 148.		11
79	Optical quenching of photoconductivity in undoped n-GaN. Journal of Applied Physics, 2004, 95, 1081-1088.	2.5	11
80	Determination of residual stress in low-temperature PECVD silicon nitride thin films. , 2004, 5276, 451.		11
81	High-resolution X-ray diffraction studies of molecular beam epitaxy-grown HgCdTe heterostructures and CdZnTe substrates. Journal of Electronic Materials, 2005, 34, 795-803.	2.2	11
82	Materials and Processes for MEMS-Based Infrared Microspectrometer Integrated on HgCdTe Detector. IEEE Journal of Selected Topics in Quantum Electronics, 2008, 14, 1031-1041.	2.9	11
83	Long-term environmental stability of residual stress of SiN _x , SiO _x , and Ge thin films prepared at low temperatures. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2009, 163, 26-30.	3.5	11
84	Characterization of low-temperature bulk micromachining of silicon using an SF ₆ /O ₂ inductively coupled plasma. Journal of Micromechanics and Microengineering, 2012, 22, 095005.	2.6	11
85	Large-Area MEMS-Based Distributed Bragg Reflectors for Short-Wave and Mid-Wave Infrared Hyperspectral Imaging Applications. Journal of Microelectromechanical Systems, 2015, 24, 2136-2144.	2.5	11
86	Engineering 1/f noise in porous silicon thin films for thermal sensing applications. Microporous and Mesoporous Materials, 2021, 324, 111302.	4.4	11
87	Laser beam induced current imaging of reactive ion etching induced n-type doping in HgCdTe. Journal of Electronic Materials, 1998, 27, 661-667.	2.2	10
88	Wide optical bandwidth asymmetric Fabry-Pérot reflection modulator using the quantum confined Stark effect. Journal of Applied Physics, 1998, 84, 5761-5765.	2.5	10
89	Characterisation of dark current in novel Hg _{1-x} Cd _x Te mid-wavelength infrared photovoltaic detectors based on n-on-p junctions formed by plasma-induced type conversion. Journal of Crystal Growth, 2000, 214-215, 1106-1110.	1.5	10
90	H ₂ -based dry plasma etching for mesa structuring of HgCdTe. Journal of Electronic Materials, 2000, 29, 853-858.	2.2	10

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91	Process condition dependence of mechanical and physical properties of silicon nitride thin films. Journal of Applied Physics, 2007, 102, 103517.	2.5	10
92	Incorporation and activation of arsenic in MBE-grown HgCdTe. Semiconductor Science and Technology, 2008, 23, 015014.	2.0	10
93	A Study of Sidewall Effects in HgCdTe Photoconductors Passivated with MBE-Grown CdTe. Journal of Electronic Materials, 2010, 39, 1019-1022.	2.2	10
94	Mechanochemical Synthesis and Characterization of GaN Nanocrystals. Journal of Nanoparticle Research, 2002, 4, 367-371.	1.9	9
95	Short-wavelength infrared tuneable filters on HgCdTe photoconductors. Optics Express, 2005, 13, 9683.	3.4	9
96	SWIR hyperspectral detection with integrated HgCdTe detector and tuneable MEMS filter. , 2006, 6295, 113.		9
97	Tunable Fabry-Perot filters operating in the 3 to 5 μ m range for infrared micro-spectrometer applications. , 2006, 6186, 69.		9
98	Adaptive focal plane array (AFPA) technologies for integrated infrared microsystems. , 2006, 6232, 70.		9
99	Responsivity and lifetime of resonant-cavity-enhanced HgCdTe detectors. Solid-State Electronics, 2006, 50, 1640-1648.	1.4	9
100	Photoluminescence of HgTe \cdot Hg $_{1-x}$ Cd $_x$ Te superlattices and a study of minibands. Physical Review B, 2007, 75, .	3.2	9
101	MWIR HgCdTe Photodiodes based on high-density plasma-induced type conversion. Semiconductor Science and Technology, 2008, 23, 095027.	2.0	9
102	Arsenic δ -doped HgTe \cdot HgCdTe superlattices grown by molecular beam epitaxy. Applied Physics Letters, 2008, 92, 082107.	3.3	9
103	A novel technique for degenerate p-type doping of germanium. Solid-State Electronics, 2013, 89, 146-152.	1.4	9
104	Investigation of crystallized germanium thin films and germanium/silicon heterojunction devices for optoelectronic applications. Materials Science in Semiconductor Processing, 2015, 30, 413-419.	4.0	9
105	Unusually strong excitonic absorption in molecular-beam-epitaxy-grown, chemically lifted GaAs thin films. Physical Review B, 1990, 42, 9496-9500.	3.2	8
106	Multiple-quantum-well reflection modulator using a lifted-off GaAs/AlGaAs film bonded to gold on silicon. Electronics Letters, 1991, 27, 557.	1.0	8
107	Magneto-Transport Characterization of p-Type HgCdTe. Journal of Electronic Materials, 2007, 36, 826-831.	2.2	8
108	Vertical transport in InAs/GaSb type-II strained layer superlattices for infrared focal plane array applications. , 2011, , .		8

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109	Dependence of ohmic contact quality on Au-Ge alloy-thickness for n-type GaAs. International Journal of Electronics, 1984, 57, 729-736.	1.4	7
110	Au-Ge-Ni migration affected by operating conditions of GaAs FETs. Solid-State Electronics, 1984, 27, 447-452.	1.4	7
111	Strain effects in chemically lifted GaAs thin films. Physical Review B, 1990, 41, 7749-7754.	3.2	7
112	Resonant cavity-enhanced mercury cadmium telluride detectors. Journal of Electronic Materials, 2004, 33, 604-608.	2.2	7
113	Some new concepts of heat-flow spreading in GaAs FET structures. International Journal of Electronics, 1984, 57, 155-160.	1.4	6
114	Variable MEMS-based inductors fabricated from PECVD silicon nitride. , 0, , .		6
115	Laser-beam-induced current mapping of spatial nonuniformities in molecular beam epitaxy As-grown HgCdTe. Journal of Electronic Materials, 2004, 33, 572-578.	2.2	6
116	Characterization of crosstalk in HgCdTe n-on-p photovoltaic infrared arrays. , 2004, , .		6
117	Effect of 60 Co gamma-irradiation on two-dimensional electron gas transport and device characteristics of AlGaIn/GaN HEMTs. Physica Status Solidi C: Current Topics in Solid State Physics, 2005, 2, 2581-2584.	0.8	6
118	A monolithically integrated HgCdTe SWIR photodetector and tunable MEMS-based optical filter. , 2005, 5783, 719.		6
119	Evaluation of plasma deposited silicon nitride thin films for microsystems technology. Journal of Microelectromechanical Systems, 2005, 14, 971-977.	2.5	6
120	Determination of HgCdTe elasto-plastic properties using nanoindentation. Journal of Electronic Materials, 2006, 35, 1197-1205.	2.2	6
121	Extending the tuning range of SWIR microspectrometers. , 2007, , .		6
122	Elasto-plastic characterisation of low-temperature plasma-deposited silicon nitride thin films using nanoindentation. International Journal of Surface Science and Engineering, 2009, 3, 3.	0.4	6
123	Nanostructural Characteristics and Mechanical Properties of Low Temperature Plasma Enhanced Chemical Vapor Deposited Silicon Nitride Thin Films. Journal of Nanoscience and Nanotechnology, 2009, 9, 3734-3741.	0.9	6
124	Integrated Resonant Optical Readout Applicable to Large Arrays of MEMS Beams. IEEE Photonics Technology Letters, 2012, 24, 2243-2246.	2.5	6
125	Effect of CdS Processing Conditions on the Properties of CdS/Si Diodes and CdS/CdTe Thin-Film Solar Cells. IEEE Journal of Photovoltaics, 2015, 5, 1783-1790.	2.5	6
126	Optimization of ICPCVD Amorphous Silicon for Optical MEMS Applications. Journal of Microelectromechanical Systems, 2015, 24, 1998-2007.	2.5	6

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127	Ultrathin-film ohmic contacts for GaAs FET. Journal Physics D: Applied Physics, 1983, 16, L243-L245.	2.8	5
128	A simplified fabrication process for HgCdTe photoconductive detectors using CH ₄ /H ₂ reactive-ion-etching-induced blocking contacts. Semiconductor Science and Technology, 2001, 16, 455-462.	2.0	5
129	Investigation of laser beam-induced current techniques for heterojunction photodiode characterization. Journal of Applied Physics, 2005, 98, 034501.	2.5	5
130	Investigation of HgTe-HgCdTe superlattices by high-resolution X-ray diffraction. Journal of Electronic Materials, 2006, 35, 1481-1486.	2.2	5
131	MEMS-based Fabry-Perot microspectrometers for agriculture. Proceedings of SPIE, 2009, , .	0.8	5
132	Silicon-Air-Silicon Distributed Bragg Reflectors for Visible and Near Infrared Optical MEMS. Journal of Microelectromechanical Systems, 2015, 24, 1245-1247.	2.5	5
133	Photostriction actuation of silicon-germanium bilayer cantilevers. Journal of Applied Physics, 2019, 125, .	2.5	5
134	A bistable MOSFET-type metal-tunnel insulator-semiconductor switch. IEEE Electron Device Letters, 1981, 2, 121-122.	3.9	4
135	Design of externally tuned asymmetric fibre Fabry-Perot electroabsorption optical modulators. IEE Proceedings: Optoelectronics, 1998, 145, 344-352.	0.8	4
136	<title>Tunable Fabry-Perot cavities</title>. , 2000, , .		4
137	Transferable silicon nitride microcavities. Microelectronics Journal, 2000, 31, 523-529.	2.0	4
138	Finite element analysis of tunable Fabry Perot MEMS structures. , 0, , .		4
139	Minority carrier lifetime and noise in abrupt molecular-beam epitaxy-grown HgCdTe heterostructures. Journal of Electronic Materials, 2003, 32, 639-645.	2.2	4
140	Stress Response of Low Temperature PECVD Silicon Nitride Thin Films to Cryogenic Thermal Cycling. , 0, , .		4
141	CHARACTERISTICS OF LOW TEMPERATURE PECVD SILICON NITRIDE FOR MEMS STRUCTURAL MATERIALS. International Journal of Modern Physics B, 2006, 20, 3799-3804.	2.0	4
142	Micro-electromechanical systems-based microspectrometers covering wavelengths from 1500nm to 5000nm. , 2007, , .		4
143	MEMS-based tunable Fabry-Perot filters on silicon substrates. Optoelectronic and Microelectronic Materials and Devices (COMMAD), Conference on, 2008, , .	0.0	4
144	Deposition heating effect on CdS thin films prepared by thermal evaporation for CdTe solar cells. , 2014, , .		4

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145	Suspended Large-Area MEMS-Based Optical Filters for Multispectral Shortwave Infrared Imaging Applications. <i>Journal of Microelectromechanical Systems</i> , 2015, 24, 1102-1110.	2.5	4
146	Preparation and Characterization of Cerium Substituted Bismuth Dysprosium Iron Garnets for Magneto-Optic Applications. <i>IEEE Transactions on Magnetics</i> , 2016, 52, 1-4.	2.1	4
147	A monolithic dual-band HgCdTe infrared detector structure. <i>IEEE Electron Device Letters</i> , 1997, 18, 352-354.	3.9	3
148	<title>Laser-beam-induced current technique as a quantitative tool for HgCdTe photodiode characterization</title>. , 1999, , .		3
149	Nano-indentation characterisation of PECVD silicon nitride films. , 0, , .		3
150	Chemical structure of low-temperature plasma-deposited silicon nitride thin films. , 2004, , .		3
151	Dark current modelling of midwave infrared HgCdTe gated photodiodes. , 2006, , .		3
152	MEMS-based microspectrometers for infrared sensing. , 2007, , .		3
153	Widely tunable Fabry-Perot optical filter using fixed-fixed beam actuators. , 2008, , .		3
154	OPTICAL MEMS TECHNOLOGIES FOR ELECTRICALLY TUNABLE MULTI-SPECTRAL SHORT-WAVE INFRARED SENSORS AND ARRAYS. <i>International Journal of High Speed Electronics and Systems</i> , 2008, 18, 1035-1044.	0.7	3
155	Thermally induced damages of PECVD SiNx thin films. <i>Journal of Materials Research</i> , 2011, 26, 2552-2557.	2.6	3
156	Near band-edge field-dependent absorption coefficient and refractive index determined by photocurrent and transmittance measurements. <i>Applied Optics</i> , 1999, 38, 5127.	2.1	2
157	<title>Anomalous drain current-voltage characteristics in AlGaIn/GaN MODFETs at low temperatures</title>. , 1999, , .		2
158	RIE-induced n-on-p junction HgCdTe photodiodes: effects of passivant technology on bake stability. , 2001, 4454, 106.		2
159	The effects of vacuum baking on the I-V characteristics of LWIR HgCdTe photodiodes. , 2004, , .		2
160	Uniformity in HgCdTe diode arrays fabricated by reactive ion etching. <i>Journal of Electronic Materials</i> , 2004, 33, 141-145.	2.2	2
161	Accurate determination of composition profiles in abrupt MBE-grown HgCdTe heterostructures. , 2004, , .		2
162	Fabry-Perot MEMS microspectrometers spanning the SWIR and MWIR. , 2007, , .		2

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163	Photoresponse in photoconductor devices fabricated from HgTe-HgCdTe superlattices. Applied Physics Letters, 2011, 98, 043505.	3.3	2
164	Electrical type conversion of p-type HgCdTe induced by nanoimprinting. Journal of Applied Physics, 2011, 109, 096102.	2.5	2
165	Fabrication process for optically low loss Si cantilever waveguide. , 2011, , .		2
166	Modeling and Design of a Thin-Film CdTe/Ge Tandem Solar Cell. Journal of Electronic Materials, 2012, 41, 2759-2765.	2.2	2
167	Recent developments towards low-cost MEMS spectrometers. , 2014, , .		2
168	Characterization and Modeling of Photostriction in Silicon Cantilevers Fabricated on Silicon-on-Insulator Substrates. Journal of Microelectromechanical Systems, 2015, 24, 182-191.	2.5	2
169	<title>Transferable silicon nitride microcavities</title>. , 1999, 3892, 142.		1
170	Anomalous drain currentâ€“voltage characteristics in AlGaIn/GaN MODFETs at low temperatures. Microelectronics Journal, 2000, 31, 531-536.	2.0	1
171	Towards a laser beam induced current test structure for the nondestructive determination of junction depth in HgCdTe photodiodes. , 0, , .		1
172	Diffusion length measurements using laser beam induced current. , 0, , .		1
173	<title>60Co gamma-irradiation-induced defects in MOCVD n-GaN</title>. , 2001, , .		1
174	Non-contact evaluation of photodiode performance by laser beam induced current imaging. , 0, , .		1
175	Noise modeling in HgCdTe heterostructure devices. Journal of Applied Physics, 2003, 94, 6541-6548.	2.5	1
176	Investigation of Surface Passivation of HgCdTe MWIR Photodiode Arrays via a Flood Illumination Technique. , 0, , .		1
177	Mechanical Design and Finite Element Analysis of Tunable Fabry-Perot MEMS Structures for Adaptive Infrared Detectors. , 0, , .		1
178	High density plasma processing of p-Hg^{0.7}Cd^{0.3}Te. , 2006, , .		1
179	Design and optimisation of a MEMS-based tunable Fabry-PÃ©rot infrared filter. , 2006, , .		1
180	Thermal Stability of PECVD SiN/sub x/ Films. , 2006, , .		1

#	ARTICLE	IF	CITATIONS
181	Characterisation of arsenic doped HgCdTe grown by Molecular Beam Epitaxy. , 2006, , .		1
182	Crystallization and compositional changes in amorphous PECVD SiN x thin films. , 2007, , .		1
183	Real-time mass spectroscopy of reflected fluxes during molecular beam epitaxy growth of HgCdTe. Journal of Vacuum Science & Technology B, 2008, 26, 1068.	1.3	1
184	HgCdTe technology in Australia. Proceedings of SPIE, 2009, , .	0.8	1
185	Capacitive sensing circuit for closed-loop control of wide tuning range microspectrometers. , 2010, , .		1
186	Recent advances in SWIR MEMS-based tunable Fabry-Pérot microspectrometers. , 2011, , .		1
187	Optical read-out scheme based on grating waveguide cantilever cavity resonance for interrogation of cantilever sensor arrays. , 2012, , .		1
188	Control of chemical composition of rare-earth substituted iron garnets using biased target deposition. , 2012, , .		1
189	Tailoring anchor shape during release of MEMS microbeams using microfluidic flow. , 2012, , .		1
190	Long-wavelength infrared Fabry-Perot etalon for multi-spectral thermal imaging. , 2013, , .		1
191	A versatile instrumentation system for MEMS-based device optical characterization. , 2013, , .		1
192	A silicon based surface micro-machined distributed Bragg reflector for MEMS spectroscopic applications. , 2013, , .		1
193	Characterization of mechanical, optical and structural properties of bismuth oxide thin films as a write-once medium for blue laser recording. Materials Research Society Symposia Proceedings, 2014, 1633, 87-92.	0.1	1
194	Tailoring Anchor Etching Profiles During MEMS Release Using Microfluidic Sheathed Flow. Journal of Microelectromechanical Systems, 2014, 23, 918-926.	2.5	1
195	Substrate heating effects on properties of CdS thin films prepared by thermal evaporation for photovoltaic applications. , 2015, , .		1
196	<title>Long-wavelength infrared photoconductor technology based on epitaxially grown Hg _{1-x} Cd _x Te</title>. , 1995, , .		0
197	<title>Status of MWIR HgCdTe photovoltaic detector technology in Australia</title>. , 1995, 2552, 110.		0
198	<title>Excess noise in MWIR photovoltaic detectors fabricated using a new junction formation technology</title>. , 1999, 3892, 221.		0

#	ARTICLE	IF	CITATIONS
199	Charge trapping centres in $\hat{1}^3$ -irradiated Gallium Nitride grown by MOCVD. , 0, , .		0
200	Modelling output admittance frequency dispersion in AlGaIn/GaN MODFETs. , 0, , .		0
201	Hydrogenation of ZnS passivation for HgCdTe. , 0, , .		0
202	Stress relaxation mechanisms in mismatched epitaxial growth of HgCdTe. , 0, , .		0
203	An inexpensive midwave infrared HgCdTe camera. , 0, , .		0
204	Characterisation of reactive ion etching induced type conversion in HgCdTe. , 0, , .		0
205	Kinetics of persistent photoconductivity in GaN grown by MOCVD. , 0, , .		0
206	Temperature stability of HgCdTe n-on-p junctions formed by reactive ion etching. , 0, , .		0
207	<title>Mobility spectrum techniques for characterizing multilayer semiconductor structures</title>. , 2001, , .		0
208	Effects of Band Tail Absorption on AlGaIn-Based Ultraviolet Photodiodes. Physica Status Solidi A, 2001, 188, 311-315.	1.7	0
209	Nondestructive determination of p-n junction depth using laser beam induced current and lateral photovoltage measurements. , 0, , .		0
210	HgCdTe long-wavelength infrared photovoltaic detectors formed by reactive ion etching. , 2002, 4795, 146.		0
211	Minority carrier lifetime in abrupt MBE grown HgCdTe heterostructures. , 2002, , .		0
212	Minority carrier behaviour in abrupt MBE grown HgCdTe heterostructures. , 0, , .		0
213	Modelling of dark currents in LWIR HgCdTe photodiodes. , 0, , .		0
214	Small HgCdTe infrared detector arrays from UWA. , 0, , .		0
215	Characterisation of MBE Grown HgCdTe Using Scanning Laser Microscopy. , 0, , .		0
216	Mercury Cadmium Telluride/Cadmium Telluride Distributed Bragg Reflectors. , 0, , .		0

#	ARTICLE	IF	CITATIONS
217	Reciprocal Space Mapping of MBE-Grown HgCdTe Heterostructures. , 0, , .		0
218	Structural and Optical Characterisation of. , 0, , .		0
219	Strain Evaluation of Plasma-Deposited Silicon Nitride. , 0, , .		0
220	Magnetoresistance characteristics of gamma-irradiated Al 0.35 Ga 0.65 N/GaN HFETs. , 2004, 5274, 152.		0
221	Refractive index engineering for a distributed Bragg reflector for a resonant-cavity-enhanced detector. , 2004, , .		0
222	MEMS based tunable infrared sensors (Invited Paper). , 2005, 5840, 91.		0
223	Resonant cavity enhanced HgCdTe detectors. , 2005, , .		0
224	Optical Performance of a MEMS Tunable IR Microspectrometer. , 2006, , .		0
225	Annealing and Shunting in RCE HgCdTe Photoconductors. , 2006, , .		0
226	Strain and orientation effects in mercury cadmium telluride grown by molecular beam epitaxy. , 2006, , .		0
227	Doubly-Supported Beam Actuators for MEMS-based Tunable Fabry-Perot Etalons. , 2006, , .		0
228	Resonant-cavity-enhanced HgCdTe photodetectors. , 2006, , .		0
229	Carrier transport characterization of high-density plasma-induced p-to-n type converted MWIR HgCdTe material. , 2006, , .		0
230	Responsivity and Lifetime of Resonant-cavity-enhanced HgCdTe photodetectors. , 2006, , .		0
231	Nano-Porous Silicon antireflection coatings for microlens application. , 2006, , .		0
232	Structural Materials for NEMS/MEMS Devices. , 2006, , .		0
233	Mechanical characteristics of filter structures for MEMS adaptive infrared detectors. , 2007, , .		0
234	1/f noise in HgCdTe infrared gated photodiodes. , 2007, , .		0

#	ARTICLE	IF	CITATIONS
235	Optical and Structural Properties of CdTe Grown by Molecular Beam Epitaxy at Low Temperature for Resonant-Cavity-Enhanced HgCdTe Detectors. Journal of Electronic Materials, 2007, 36, 877-883.	2.2	0
236	Sidewall effects of MBE grown CdTe for MWIR HgCdTe photoconductors. Optoelectronic and Microelectronic Materials and Devices (COMMAD), Conference on, 2008, , .	0.0	0
237	Laser beam induced current for qualitative evaluation of HgCdTe van der Pauw sample uniformity. Optoelectronic and Microelectronic Materials and Devices (COMMAD), Conference on, 2008, , .	0.0	0
238	Various annealing methods for activation of arsenic in Molecular Beam Epitaxy grown HgCdTe. Optoelectronic and Microelectronic Materials and Devices (COMMAD), Conference on, 2008, , .	0.0	0
239	Effect of heat treatment on internal stresses in PECVD SiNxHy thin films. Optoelectronic and Microelectronic Materials and Devices (COMMAD), Conference on, 2008, , .	0.0	0
240	HgCdTe MWIR PECVD SiN passivated photodiodes. Optoelectronic and Microelectronic Materials and Devices (COMMAD), Conference on, 2008, , .	0.0	0
241	Recent developments in MEMS-based tunable IR detectors. , 2008, , .		0
242	Cross-flow microfiltration for lab-on-chip defatting of human breast milk. Proceedings of SPIE, 2008, , .	0.8	0
243	Electron magnetoresistance mobility in silicon on insulator layers using Kelvin's technique. , 2009, , .		0
244	Performance predictions for monolithic thin-film CdTe/Ge tandem solar cells. , 2010, , .		0
245	Electron magnetoresistance mobility in silicon-on-insulator layers using Kelvin's technique. Solid-State Electronics, 2010, 54, 1047-1050.	1.4	0
246	Dispersion of lanthanum hexaboride nanoparticles in water and in sol-gel silica arrays. , 2010, , .		0
247	Optical MEMS technologies for multi-spectral infrared sensors. , 2010, , .		0
248	Comparison of dynamic and static operation of a novel optical read-out technology for micromachined cantilever sensors. , 2010, , .		0
249	Nanoimprint induced electrical type conversion in HgCdTe. , 2010, , .		0
250	On the accuracy of decay constant measurement by swept-cavity heterodyne cavity ringdown spectroscopy. Proceedings of SPIE, 2011, , .	0.8	0
251	A novel optical read-out technology for large arrays of micromachined cantilever sensors. , 2011, , .		0
252	Demonstration of a method for detecting MEMS suspended beam height. , 2012, , .		0

#	ARTICLE	IF	CITATIONS
253	A WDM Capable Integrated Optical Readout of a MEMS Sensor. Procedia Engineering, 2012, 47, 386-389.	1.2	0
254	Single crystal and amorphous Ge for use in stand-alone and thin film tandem solar cells. , 2012, , .		0
255	An optically resonant, grating-based technique for the sensitive detection of MEMS cantilever beam height. , 2012, , .		0
256	Mobility spectrum analysis of p-to-n type converted vacancy doped HgCdTe. , 2012, , .		0
257	Plasma annealing as an effective method for the crystallization of bismuth iron garnet films. , 2012, , .		0
258	Effect of FIB milling on MEMS SOI cantilevers. , 2012, , .		0
259	Macromodel for the transient simulation of electrostatically actuated fixed-fixed beams. , 2013, , .		0
260	Optical actuation of silicon cantilevers: modelling and experimental investigation. , 2013, , .		0
261	Targeted sacrificial layer etching for MEMS release using microfluidic channels. , 2013, , .		0
262	Microcantilevers as a platform for the detection of hydrogen. , 2014, , .		0
263	Strain simulation and MBE growth of CdTe on GaSb substrates. , 2014, , .		0
264	Targeted machining during MEMS device fabrication using PDMS microfluidic cassettes. , 2014, , .		0
265	Characterisation of SiN _x -HgCdTe interface in metal-insulator-semiconductor structure. , 2014, , .		0
266	High Resolution Position Monitoring of Suspended MEMS towards Biological and Chemical Sensors. Materials Research Society Symposia Proceedings, 2014, 1659, 9-14.	0.1	0
267	An optically resonant position read-out system for MEMS gas sensors. , 2014, , .		0
268	An optical MEMS cross-bar switch. , 2016, , .		0
269	Recent developments towards low-cost miniaturized IR spectrometers for field applications. , 2012, , .		0